



# BUK9875-100A

## N-channel TrenchMOS logic level FET

19 March 2014

Product data sheet

## 1. General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

## 2. Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant
- Suitable for logic level gate drive sources

## 3. Applications

- 12 V, 24 V and 42 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

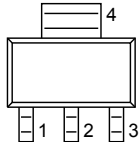
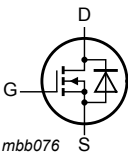
## 4. Quick reference data

Table 1. Quick reference data

| Symbol                 | Parameter                                    | Conditions                                                                                                                             |  | Min | Typ | Max | Unit |
|------------------------|----------------------------------------------|----------------------------------------------------------------------------------------------------------------------------------------|--|-----|-----|-----|------|
| V <sub>DS</sub>        | drain-source voltage                         | T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 150 °C                                                                                        |  | -   | -   | 100 | V    |
| I <sub>D</sub>         | drain current                                | V <sub>GS</sub> = 5 V; T <sub>sp</sub> = 25 °C; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>                                        |  | -   | -   | 7   | A    |
| P <sub>tot</sub>       | total power dissipation                      | T <sub>sp</sub> = 25 °C; <a href="#">Fig. 1</a>                                                                                        |  | -   | -   | 8   | W    |
| Static characteristics |                                              |                                                                                                                                        |  |     |     |     |      |
| R <sub>DSon</sub>      | drain-source on-state resistance             | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 8 A; T <sub>j</sub> = 25 °C                                                                  |  | -   | -   | 84  | mΩ   |
|                        |                                              | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 8 A; T <sub>j</sub> = 25 °C                                                                   |  | -   | 62  | 72  | mΩ   |
|                        |                                              | V <sub>GS</sub> = 5 V; I <sub>D</sub> = 8 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>                 |  | -   | 64  | 75  | mΩ   |
| Avalanche ruggedness   |                                              |                                                                                                                                        |  |     |     |     |      |
| E <sub>DS(AL)S</sub>   | non-repetitive drain-source avalanche energy | I <sub>D</sub> = 7 A; V <sub>sup</sub> ≤ 100 V; R <sub>GS</sub> = 50 Ω; V <sub>GS</sub> = 5 V; T <sub>j(init)</sub> = 25 °C; unclamped |  | -   | -   | 49  | mJ   |

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline                                                                                  | Graphic symbol                                                                                |
|-----|--------|-------------|-----------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------------------------------|
| 1   | G      | gate        | <br>SC-73 (SOT223) | <br>mbb076 |
| 2   | D      | drain       |                                                                                                     |                                                                                               |
| 3   | S      | source      |                                                                                                     |                                                                                               |
| 4   | D      | drain       |                                                                                                     |                                                                                               |

## 6. Ordering information

Table 3. Ordering information

| Type number     | Package |                                                                  |         |
|-----------------|---------|------------------------------------------------------------------|---------|
|                 | Name    | Description                                                      | Version |
| BUK9875-100A    | SC-73   | plastic surface-mounted package with increased heatsink; 4 leads | SOT223  |
| BUK9875-100A/CU | SC-73   | plastic surface-mounted package with increased heatsink; 4 leads | SOT223  |

## 7. Marking

Table 4. Marking codes

| Type number     | Marking code |
|-----------------|--------------|
| BUK9875-100A    | 987510A      |
| BUK9875-100A/CU | 987510       |

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol    | Parameter               | Conditions                                                                                        | Min | Max | Unit |
|-----------|-------------------------|---------------------------------------------------------------------------------------------------|-----|-----|------|
| $V_{DS}$  | drain-source voltage    | $T_j \geq 25\text{ °C}$ ; $T_j \leq 150\text{ °C}$                                                | -   | 100 | V    |
| $V_{DGR}$ | drain-gate voltage      | $R_{GS} = 20\text{ k}\Omega$                                                                      | -   | 100 | V    |
| $V_{GS}$  | gate-source voltage     |                                                                                                   | -10 | 10  | V    |
| $P_{tot}$ | total power dissipation | $T_{sp} = 25\text{ °C}$ ; <a href="#">Fig. 1</a>                                                  | -   | 8   | W    |
| $I_D$     | drain current           | $T_{sp} = 25\text{ °C}$ ; $V_{GS} = 5\text{ V}$ ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a> | -   | 7   | A    |
|           |                         | $T_{sp} = 100\text{ °C}$ ; $V_{GS} = 5\text{ V}$ ; <a href="#">Fig. 2</a>                         | -   | 4   | A    |
| $I_{DM}$  | peak drain current      | $T_{sp} = 25\text{ °C}$ ; pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; <a href="#">Fig. 3</a>       | -   | 28  | A    |

| Symbol               | Parameter                                    | Conditions                                                                                                                             |  | Min | Max | Unit |
|----------------------|----------------------------------------------|----------------------------------------------------------------------------------------------------------------------------------------|--|-----|-----|------|
| T <sub>stg</sub>     | storage temperature                          |                                                                                                                                        |  | -55 | 150 | °C   |
| T <sub>j</sub>       | junction temperature                         |                                                                                                                                        |  | -55 | 150 | °C   |
| V <sub>GSM</sub>     | peak gate-source voltage                     | pulsed; t <sub>p</sub> ≤ 50 μs                                                                                                         |  | -15 | 15  | V    |
| Source-drain diode   |                                              |                                                                                                                                        |  |     |     |      |
| I <sub>S</sub>       | source current                               | T <sub>sp</sub> = 25 °C                                                                                                                |  | -   | 7   | A    |
| I <sub>SM</sub>      | peak source current                          | pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>sp</sub> = 25 °C                                                                                |  | -   | 28  | A    |
| Avalanche ruggedness |                                              |                                                                                                                                        |  |     |     |      |
| E <sub>DS(AL)S</sub> | non-repetitive drain-source avalanche energy | I <sub>D</sub> = 7 A; V <sub>sup</sub> ≤ 100 V; R <sub>GS</sub> = 50 Ω; V <sub>GS</sub> = 5 V; T <sub>j(init)</sub> = 25 °C; unclamped |  | -   | 49  | mJ   |

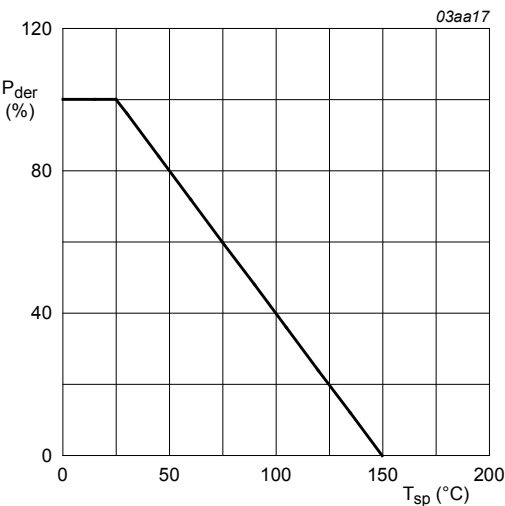


Fig. 1. Normalized total power dissipation as a function of solder point temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

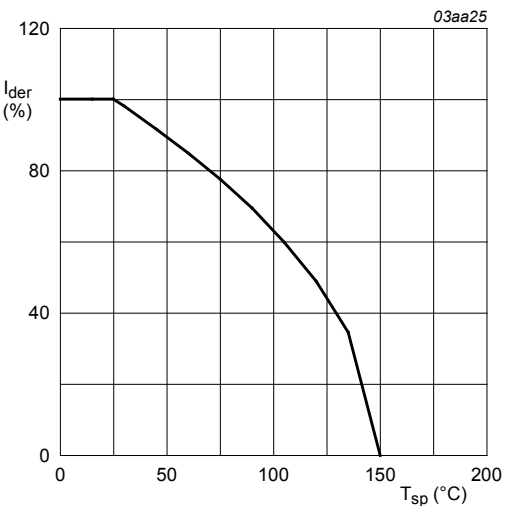


Fig. 2. Normalized continuous drain current as a function of solder point temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100\%$$

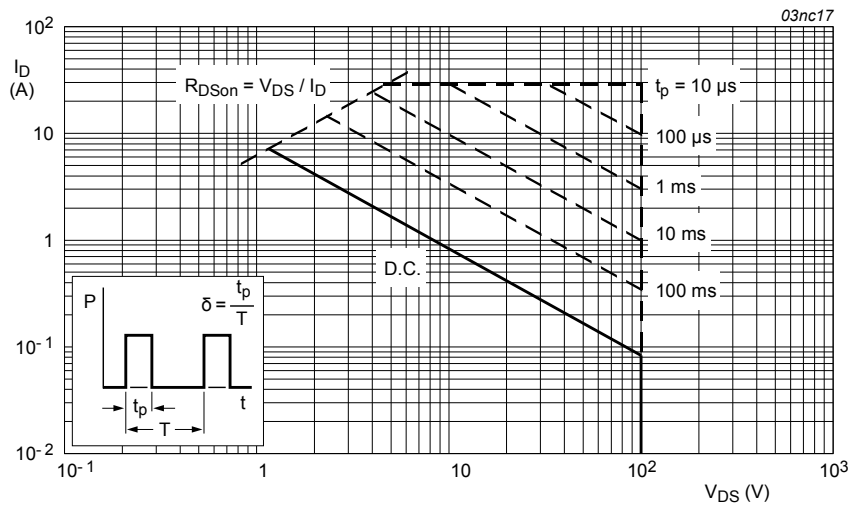


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{amb} = 25^{\circ}C$ ;  $I_{DM}$  is single pulse

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter                                        | Conditions | Min | Typ | Max | Unit |
|----------------|--------------------------------------------------|------------|-----|-----|-----|------|
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point |            | -   | -   | 15  | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient      | Fig. 4     | -   | 120 | -   | K/W  |

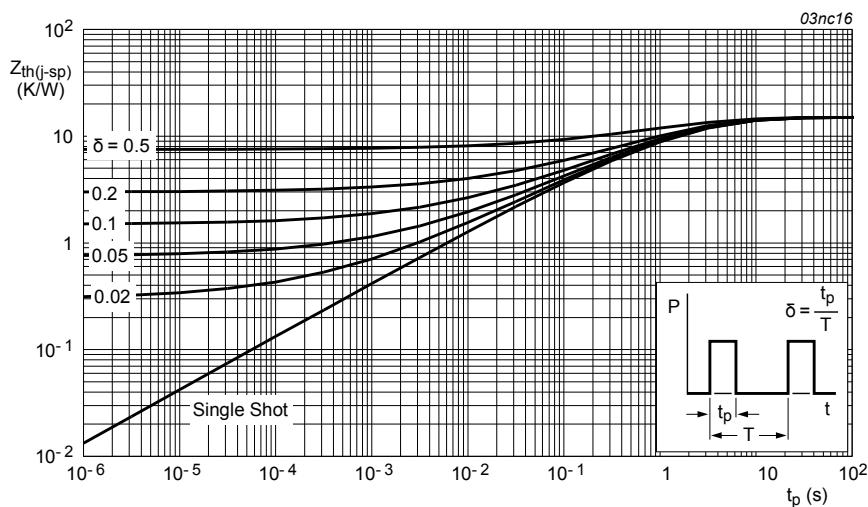


Fig. 4. Transient thermal impedance from junction to solder point as a function of pulse duration

## 10. Characteristics

Table 7. Characteristics

| Symbol                  | Parameter                        | Conditions                                                                                                                      |  | Min | Typ  | Max  | Unit |
|-------------------------|----------------------------------|---------------------------------------------------------------------------------------------------------------------------------|--|-----|------|------|------|
| Static characteristics  |                                  |                                                                                                                                 |  |     |      |      |      |
| V <sub>(BR)DSS</sub>    | drain-source breakdown voltage   | I <sub>D</sub> = 0.25 mA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                         |  | 100 | -    | -    | V    |
|                         |                                  | I <sub>D</sub> = 0.25 mA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C                                                        |  | 89  | -    | -    | V    |
| V <sub>GS(th)</sub>     | gate-source threshold voltage    | I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; <a href="#">Fig. 11</a>                      |  | 1   | 1.5  | 2    | V    |
|                         |                                  | I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; <a href="#">Fig. 11</a>                     |  | -   | -    | 2.3  | V    |
|                         |                                  | I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 150 °C; <a href="#">Fig. 11</a>                     |  | 0.6 | -    | -    | V    |
| I <sub>DSS</sub>        | drain leakage current            | V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                          |  | -   | 0.05 | 10   | μA   |
|                         |                                  | V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C                                                         |  | -   | -    | 500  | μA   |
| I <sub>GSS</sub>        | gate leakage current             | V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                           |  | -   | 2    | 100  | nA   |
|                         |                                  | V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                          |  | -   | 2    | 100  | nA   |
| R <sub>DSon</sub>       | drain-source on-state resistance | V <sub>GS</sub> = 5 V; I <sub>D</sub> = 8 A; T <sub>j</sub> = 150 °C; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>         |  | -   | -    | 162  | mΩ   |
|                         |                                  | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 8 A; T <sub>j</sub> = 25 °C                                                           |  | -   | -    | 84   | mΩ   |
|                         |                                  | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 8 A; T <sub>j</sub> = 25 °C                                                            |  | -   | 62   | 72   | mΩ   |
|                         |                                  | V <sub>GS</sub> = 5 V; I <sub>D</sub> = 8 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>          |  | -   | 64   | 75   | mΩ   |
| Dynamic characteristics |                                  |                                                                                                                                 |  |     |      |      |      |
| C <sub>iss</sub>        | input capacitance                | V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz; T <sub>j</sub> = 25 °C; <a href="#">Fig. 14</a>                       |  | -   | 1270 | 1690 | pF   |
| C <sub>oss</sub>        | output capacitance               |                                                                                                                                 |  | -   | 140  | 167  | pF   |
| C <sub>rss</sub>        | reverse transfer capacitance     |                                                                                                                                 |  | -   | 90   | 124  | pF   |
| t <sub>d(on)</sub>      | turn-on delay time               | V <sub>DS</sub> = 30 V; R <sub>L</sub> = 1.2 Ω; V <sub>GS</sub> = 5 V; R <sub>G(ext)</sub> = 10 Ω; T <sub>j</sub> = 25 °C       |  | -   | 13   | -    | ns   |
| t <sub>r</sub>          | rise time                        |                                                                                                                                 |  | -   | 120  | -    | ns   |
| t <sub>d(off)</sub>     | turn-off delay time              |                                                                                                                                 |  | -   | 58   | -    | ns   |
| t <sub>f</sub>          | fall time                        |                                                                                                                                 |  | -   | 57   | -    | ns   |
| Source-drain diode      |                                  |                                                                                                                                 |  |     |      |      |      |
| V <sub>SD</sub>         | source-drain voltage             | I <sub>S</sub> = 5 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 15</a>                                    |  | -   | 0.85 | 1.2  | V    |
| t <sub>rr</sub>         | reverse recovery time            | I <sub>S</sub> = 20 A; dI <sub>S</sub> /dt = -100 A/μs; V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 30 V; T <sub>j</sub> = 25 °C |  | -   | 63   | -    | ns   |
| Q <sub>r</sub>          | recovered charge                 |                                                                                                                                 |  | -   | 220  | -    | nC   |

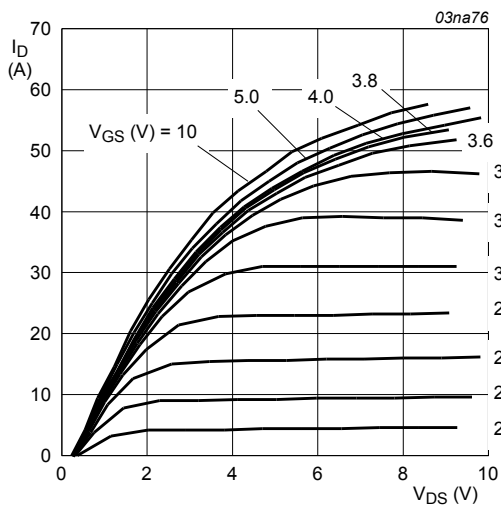


Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values

$T_j = 25^\circ\text{C}$

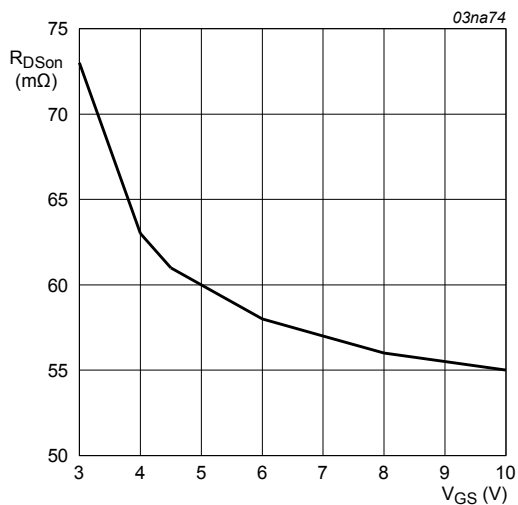


Fig. 6. Drain-source on-state resistance as a function of gate-source; typical values

$T_j = 25^\circ\text{C}; I_D = 8\text{A}$

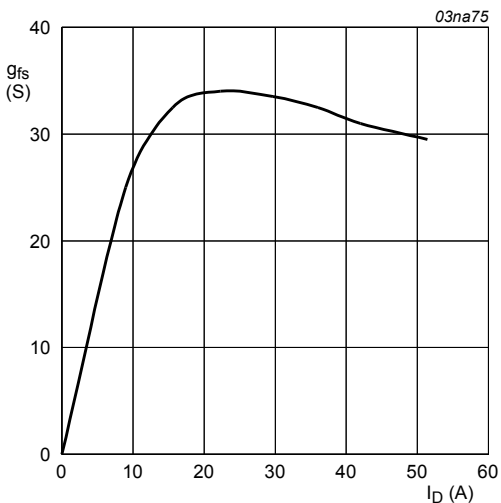


Fig. 7. Forward transconductance as a function of drain current; typical values

$T_j = 25^\circ\text{C}; V_{DS} = 25\text{V}$

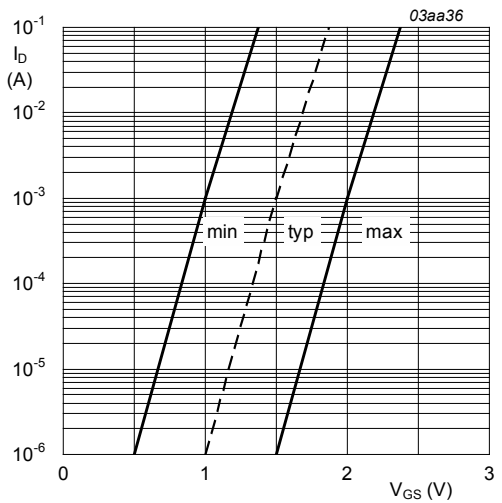


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25^\circ\text{C}; V_{DS} = 5\text{V}$

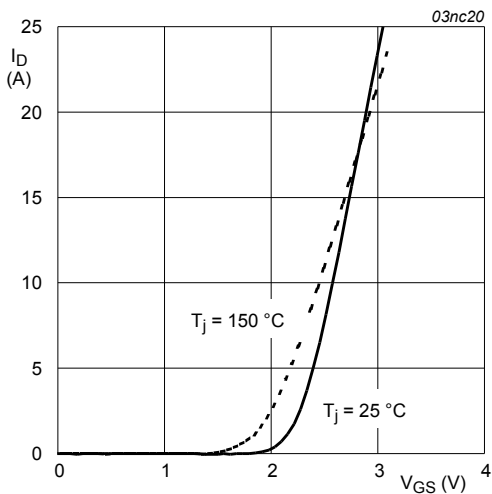


Fig. 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$V_{DS} = 25\text{ V}$

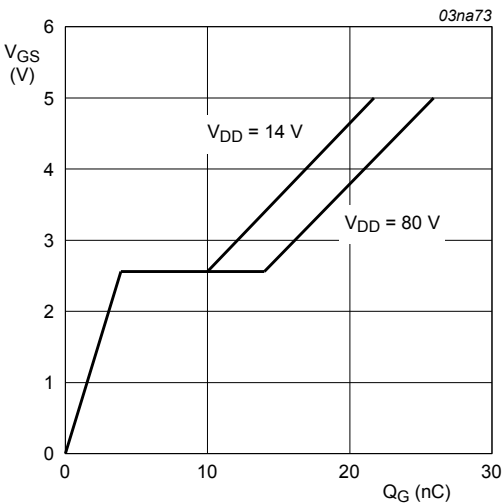


Fig. 10. Gate-source voltage as a function of turn-on gate charge; typical values

$T_j = 25\text{ }^{\circ}\text{C}; I_D = 20\text{ A}$

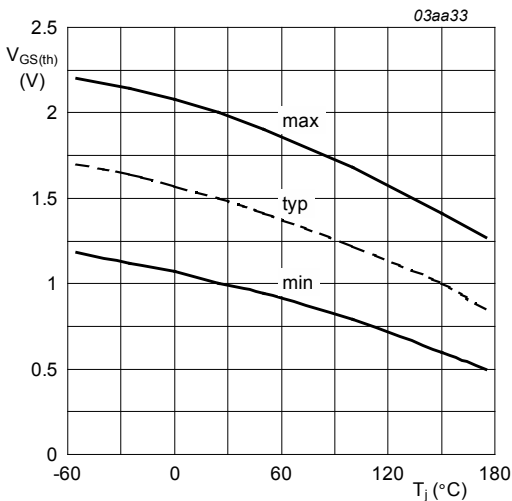


Fig. 11. Gate-source threshold voltage as a function of junction temperature

$I_D = 1\text{ mA}; V_{DS} = V_{GS}$

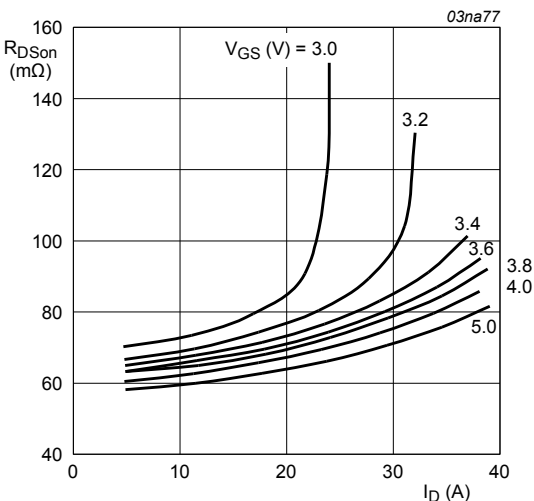


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

$T_j = 25\text{ }^{\circ}\text{C}$

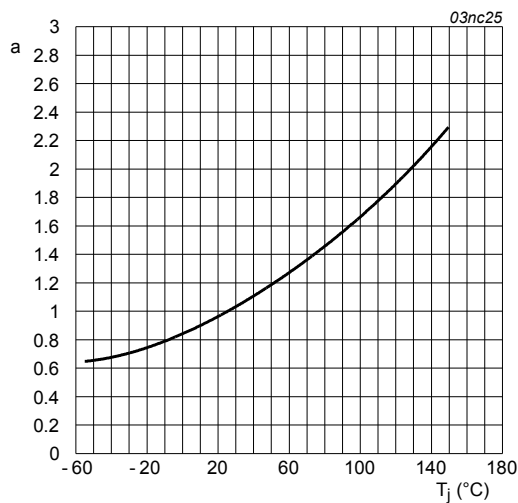


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DS(on)}}{R_{DS(on)25^{\circ}\text{C}}}$$

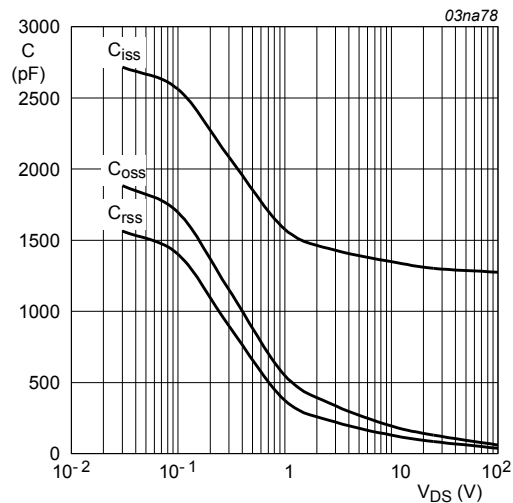


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V; f = 1\text{MHz}$$

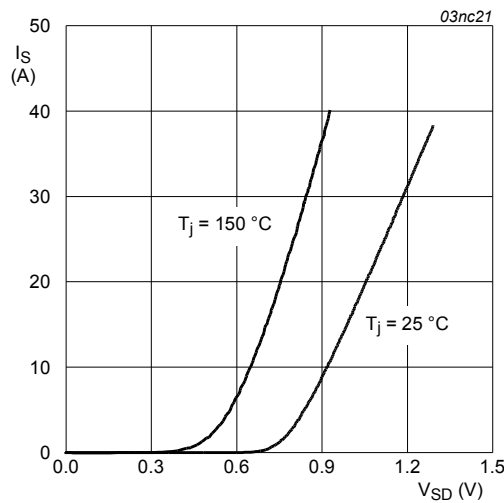


Fig. 15. Reverse diode current as a function of reverse diode voltage; typical value

$$V_{GS} = 0V$$



11. Package outline

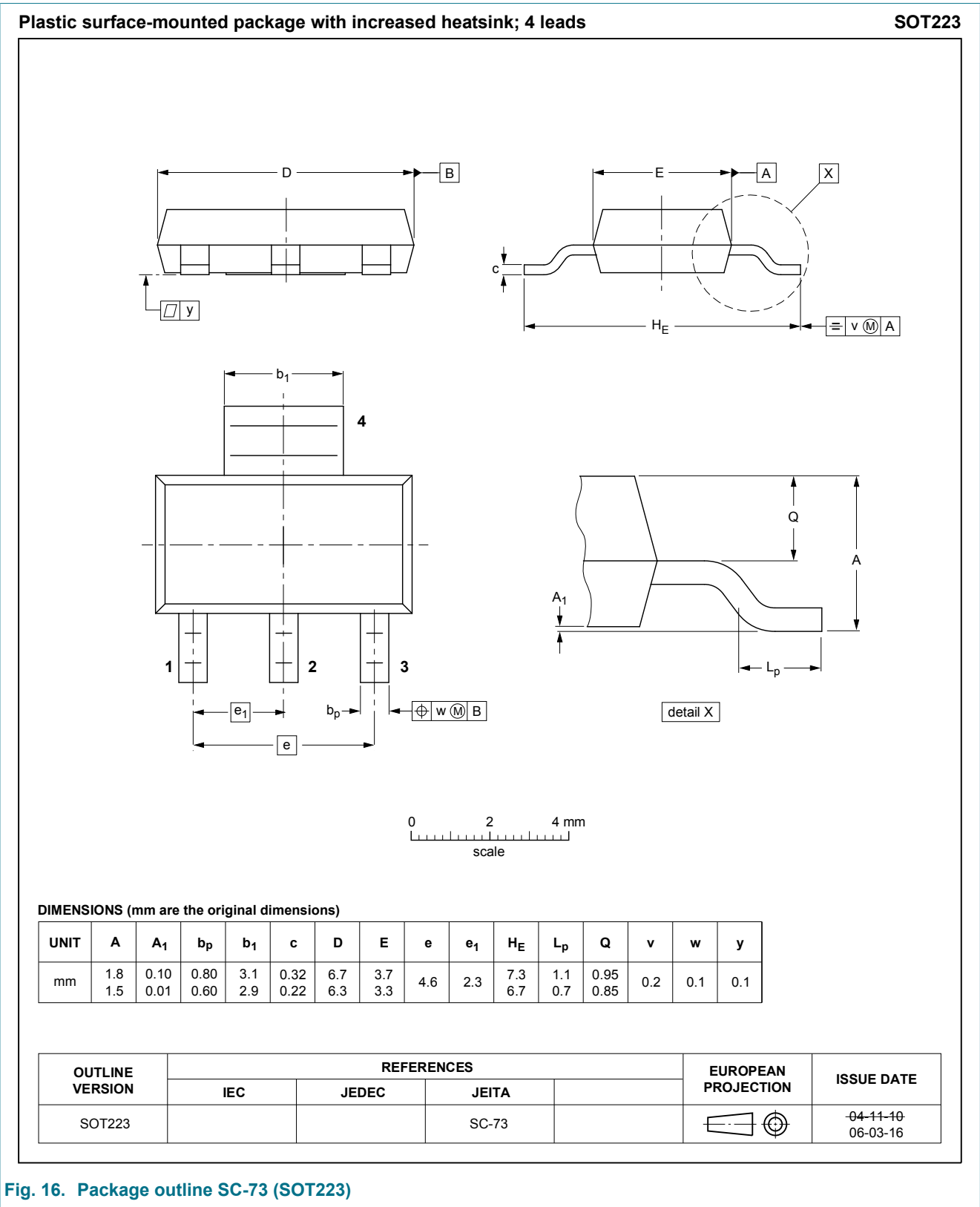


Fig. 16. Package outline SC-73 (SOT223)

## 12. Legal information

### 12.1 Data sheet status

| Document status [1][2]         | Product status [3] | Definition                                                                            |
|--------------------------------|--------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
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- [2] The term 'short data sheet' is explained in section "Definitions".
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Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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